

# NX3020NAKW

# 30 V, 180 mA N-channel Trench MOSFET

29 October 2013

**Product data sheet** 

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

### 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	180	mA
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 100 \text{ mA}; T_j = 25 \text{ °C}$		-	2.7	4.5	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1	G S 017aaa255

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX3020NAKW	SC-70	plastic surface-mounted package; 3 leads	SOT323

## 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
NX3020NAKW	%3A

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	180	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	110	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	720	mA
P <sub>tot</sub> total power dissip	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	260	mW
			[1]	-	300	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>sp</sub> = 25 °C		-	1100	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode		'			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	180	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

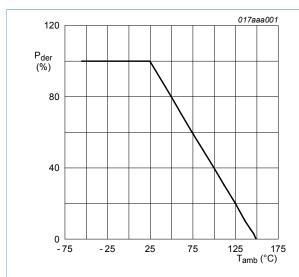


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

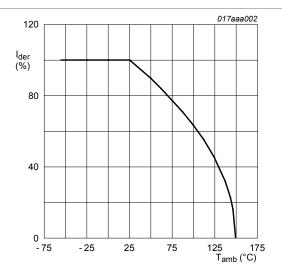


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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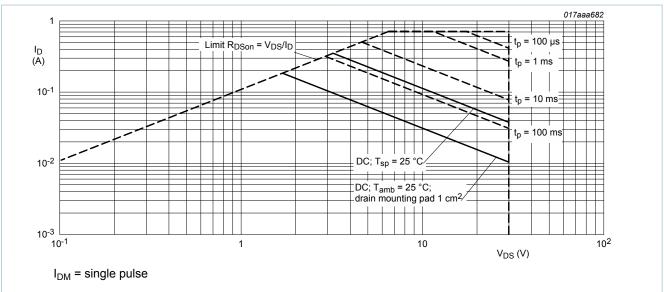


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from	thermal resistance in free air	in free air	[1]	-	415	480	K/W
	from junction to ambient		[2]	-	350	400	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	110	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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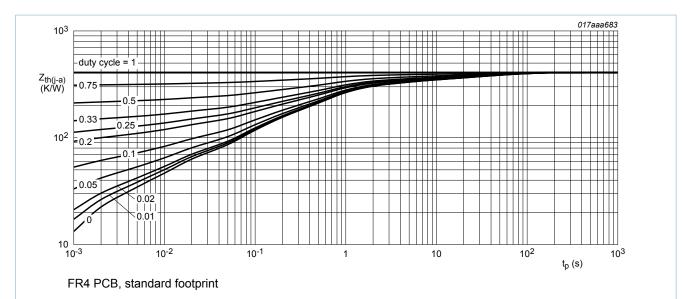


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

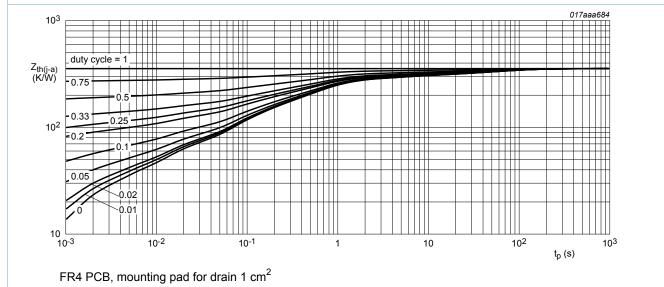


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	8.0	1.2	1.5	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3.5	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	3.5	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	0.5	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	2.7	4.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C	-	5.5	9.2	Ω
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	3	5.2	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 10 mA; T <sub>j</sub> = 25 °C	-	4	13	Ω
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 150 mA; T <sub>j</sub> = 25 °C	-	320	-	S
Dynamic c	haracteristics		'	'		,
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 150 mA; V <sub>GS</sub> = 4.5 V;	-	0.34	0.44	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.11	-	nC
$Q_{GD}$	gate-drain charge		-	0.06	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	13	20	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.1	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 ^{\circ}C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	34	68	ns
t <sub>f</sub>	fall time		-	17	-	ns
Source-dra	in diode			1	-	
$V_{SD}$	source-drain voltage	$I_S$ = 115 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	0.47	0.7	1.2	V

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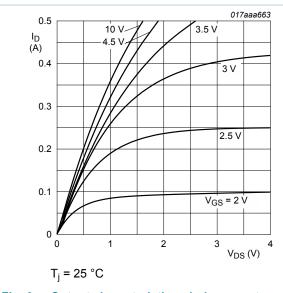


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

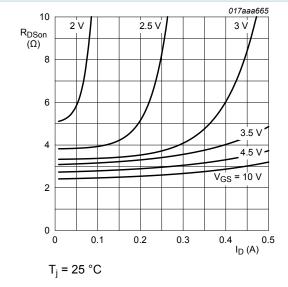


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

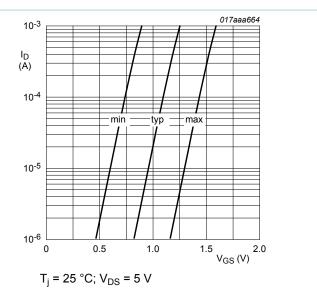


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

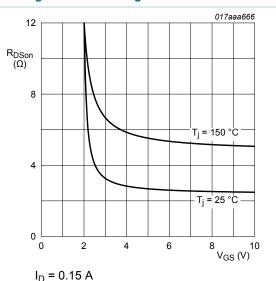


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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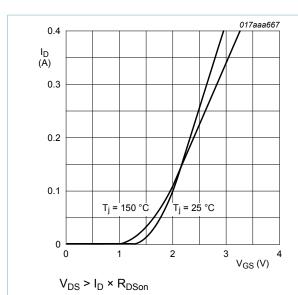


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

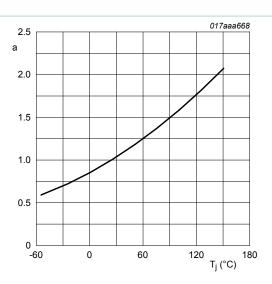


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

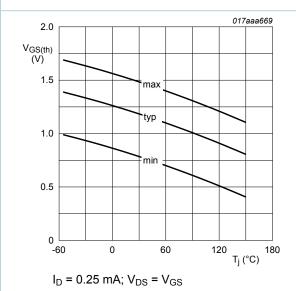
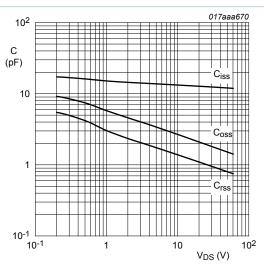


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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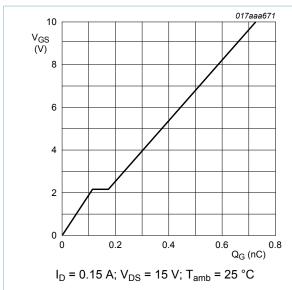


Fig. 15. Gate charge waveform definitions

Q<sub>GS1</sub>

Q<sub>GS2</sub>

Q<sub>G(tot)</sub>—Q<sub>GD</sub>—

017aaa137

V<sub>DS</sub> \_

 $V_{GS(pl)}$ 

V<sub>GS(th)</sub>



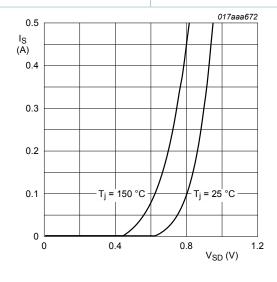
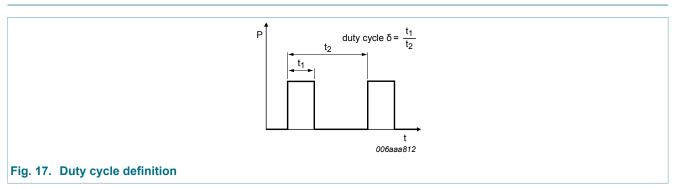


Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information

 $V_{GS} = 0 V$ 



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## 12. Package outline

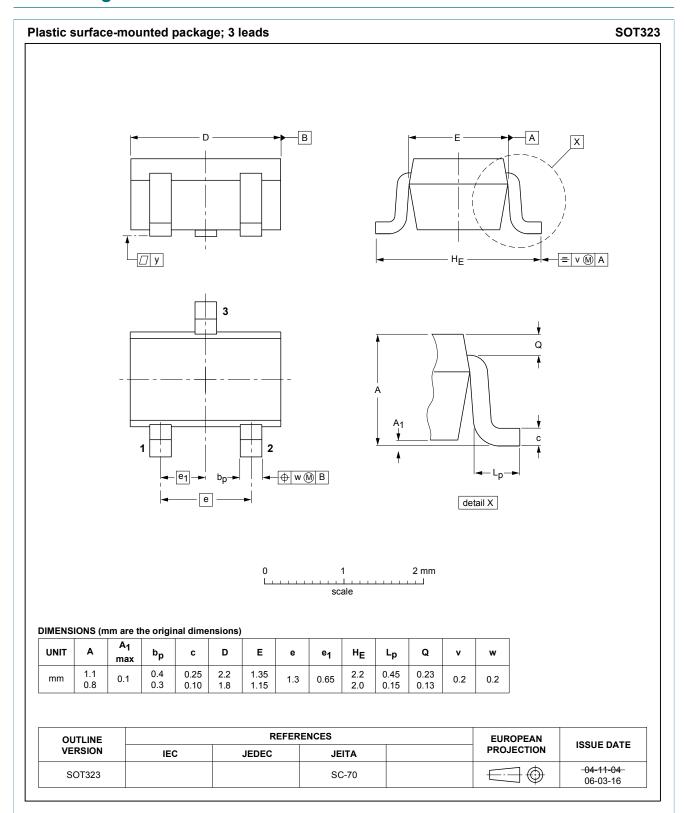
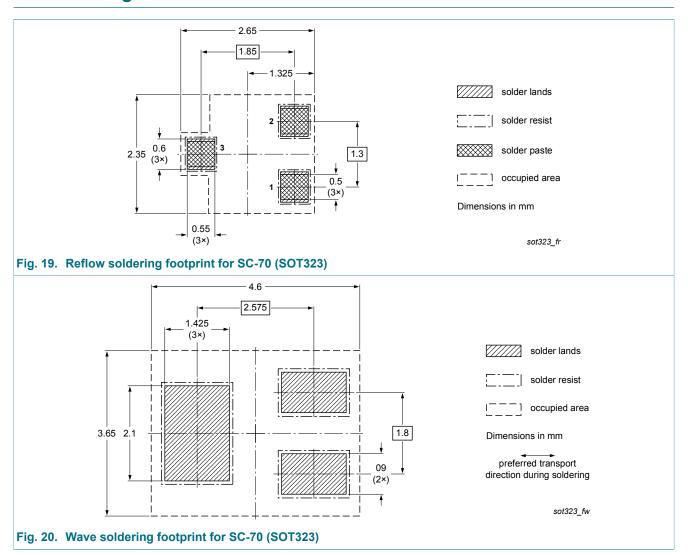


Fig. 18. Package outline SC-70 (SOT323)

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### 13. Soldering



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## 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX3020NAKW v.2	20131029	Product data sheet	-	NX3020NAKW v.1
Modifications:	<ul><li> 3D package outline</li><li> Table 7 values of ca</li><li> Figure 13 corrected</li></ul>	apacitance parameters co	prrected	
NX3020NAKW v.1	20120830	Product data sheet	-	-

#### 30 V, 180 mA N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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